

NTJS3157N

MOSFET – Power, Single, N-Channel, Trench, SC-88

20 V, 4.0 A

Features

- Leading Trench Technology for Low $R_{DS(ON)}$ Extending Battery Life
- Fast Switching for Increased Circuit Efficiency
- SC-88 Small Outline (2 x 2 mm) for Maximum Circuit Board Utilization, Same as SC-70-6
- These are Pb-Free Devices

Applications

- DC-DC Conversion
- Low Side Load Switch
- Cell Phones, Computing, Digital Cameras, MP3s and PDAs

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Symbol	Value	Unit			
Drain-to-Source Voltage	V_{DSS}	20	V			
Gate-to-Source Voltage	V_{GS}	± 8.0	V			
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	I_D	3.2	A	
		$T_A = 85^\circ\text{C}$				2.3
		$t \leq 5\text{ s}$				$T_A = 25^\circ\text{C}$
Power Dissipation (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	P_D	1.0	W	
Pulsed Drain Current		$t_p = 10\ \mu\text{s}$	I_{DM}	10	A	
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to 150			$^\circ\text{C}$	
Source Current (Body Diode)	I_S	1.6			A	
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260			$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS (Note 1)

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State	$R_{\theta JA}$	125	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5\text{ s}$	$R_{\theta JA}$	80	
Junction-to-Lead – Steady State	$R_{\theta JL}$	45	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [1 oz] including traces).

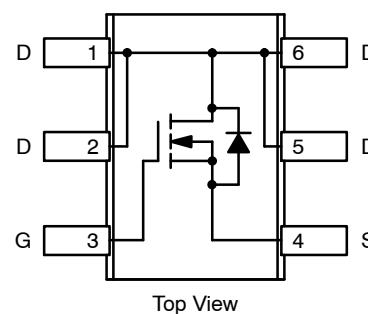


ON Semiconductor®

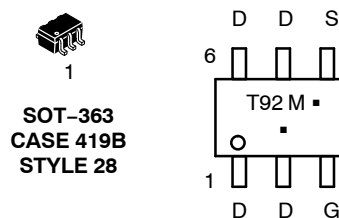
<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
20 V	45 m Ω @ 4.5 V	4.0 A
	55 m Ω @ 2.5 V	
	70 m Ω @ 1.8 V	

SC-88 (SOT-363)



MARKING DIAGRAM & PIN ASSIGNMENT



T92 = Device Code
M = Date Code
■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise stated)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J	V _{GS} = 0 V, I _D = 250 μA		12		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 16 V	T _J = 25°C		1.0	μA
			T _J = 85°C		5.0	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8.0 V			±100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	0.40		1.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J		-4.0			mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 4.0 A V _{GS} = 2.5 V, I _D = 3.6 A V _{GS} = 1.8 V, I _D = 2.0 A		45	60	mΩ
				55	70	
				70	85	
Forward Transconductance	g _{FS}	V _{GS} = 10 V, I _D = 3.2 A		9.0		S

CHARGES AND CAPACITANCES

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1.0 MHz, V _{DS} = 10 V		500		pF
Output Capacitance	C _{OSS}			75		
Reverse Transfer Capacitance	C _{RSS}			60		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 10 V, I _D = 3.2 A		6.9	15	nC
Gate-to-Source Charge	Q _{GS}			1.0		
Gate-to-Drain Charge	Q _{GD}			1.8		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	t _{d(on)}	V _{GS} = 4.5 V, V _{DD} = 10 V, I _D = 0.5 A, R _G = 6.0 Ω		6.0	15	ns
Rise Time	t _r			12	25	
Turn-Off Delay Time	t _{d(off)}			21	45	
Fall Time	t _f			11	25	

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 1.6 A	T _J = 25°C		0.7	1.0	V
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 1.6 A			15		ns
Charge Time	T _a				12		
Discharge Time	T _b				3.0		
Reverse Recovery Charge	Q _{RR}				5.0		nC

2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

3. Switching characteristics are independent of operating junction temperatures.

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TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

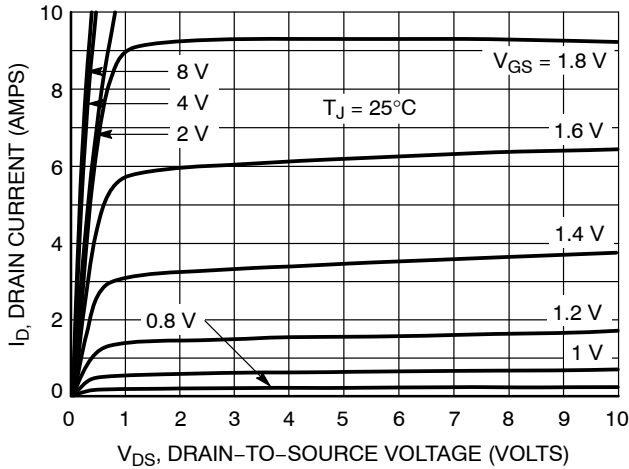


Figure 1. On-Region Characteristics

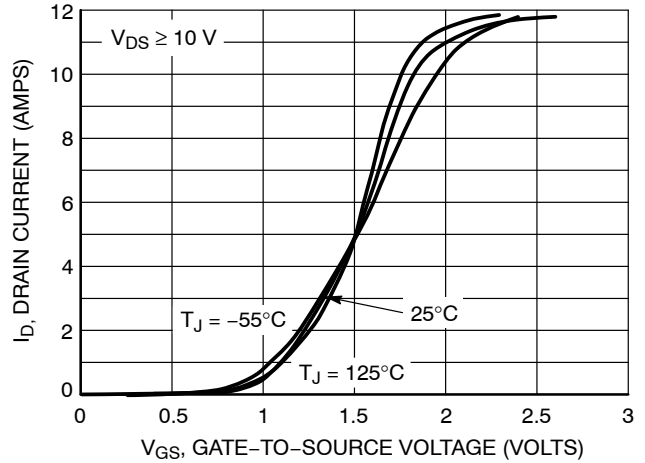


Figure 2. Transfer Characteristics

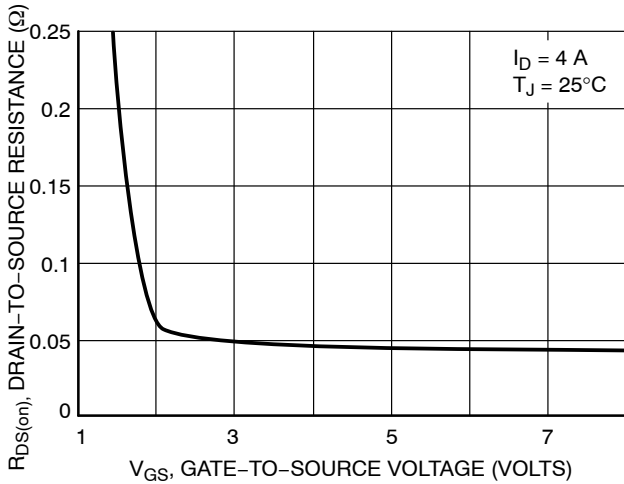


Figure 3. On-Resistance vs. Gate-to-Source Voltage

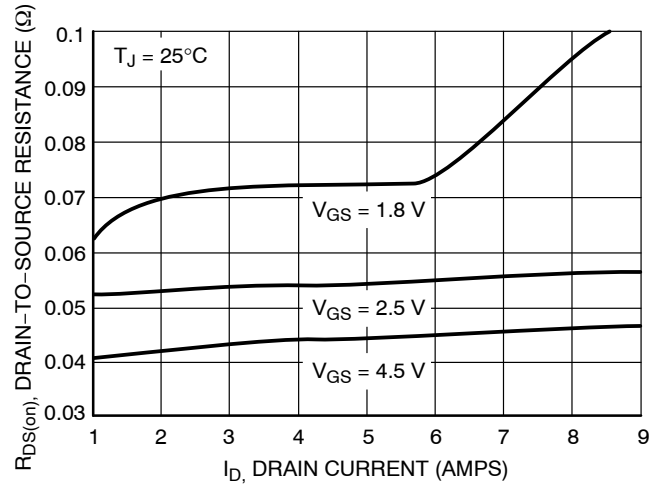


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

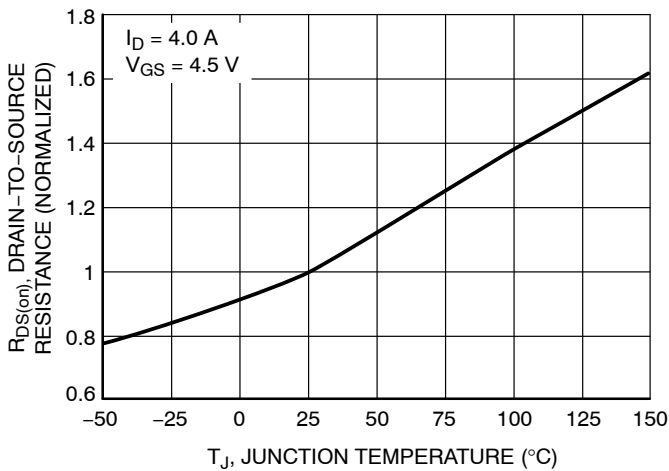


Figure 5. On-Resistance Variation with Temperature

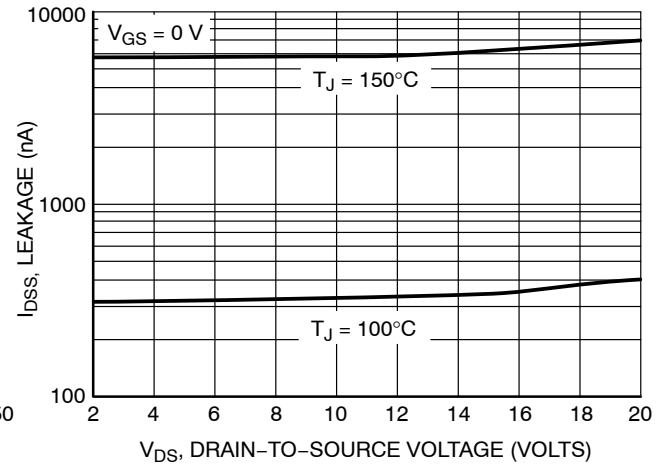


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

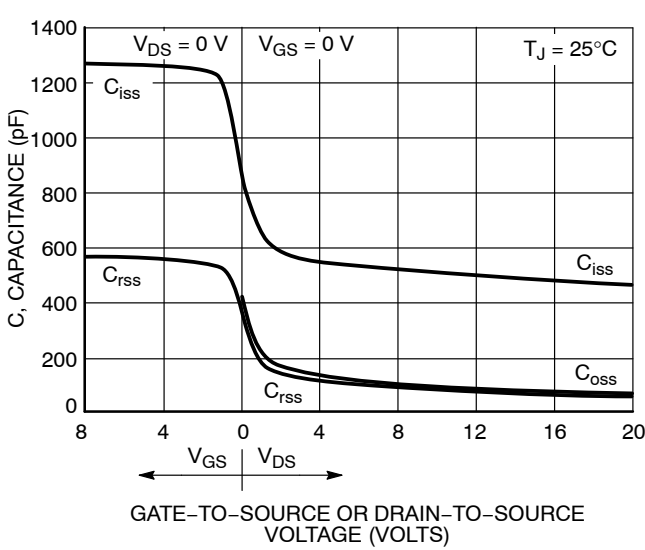


Figure 7. Capacitance Variation

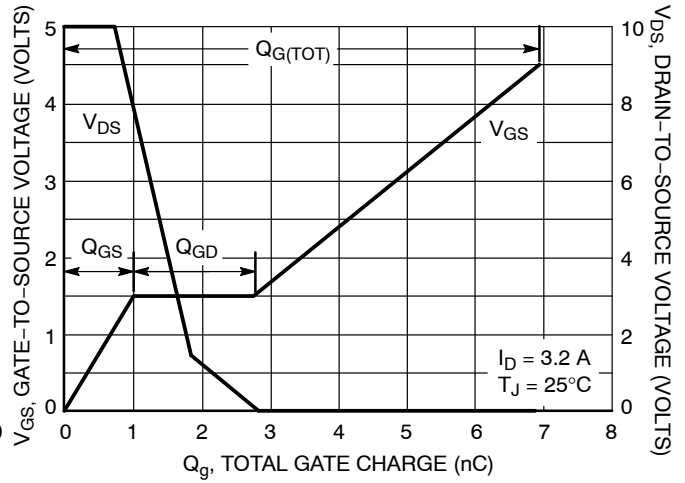


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

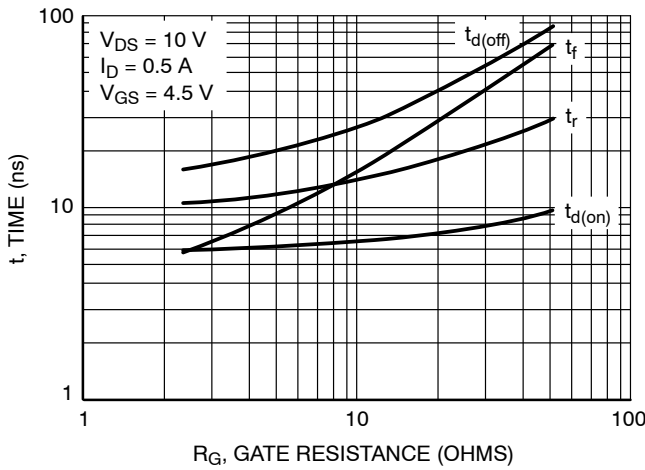


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

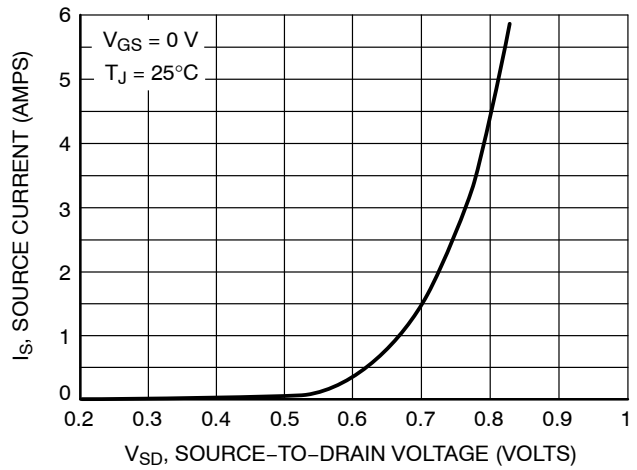


Figure 10. Diode Forward Voltage vs. Current

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ORDERING INFORMATION

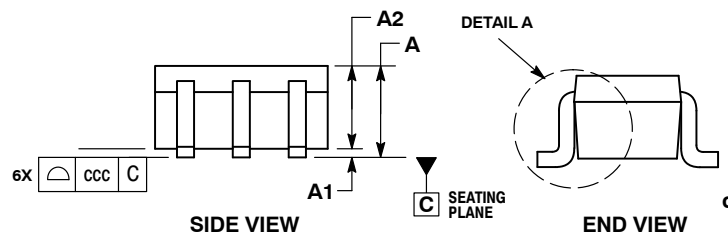
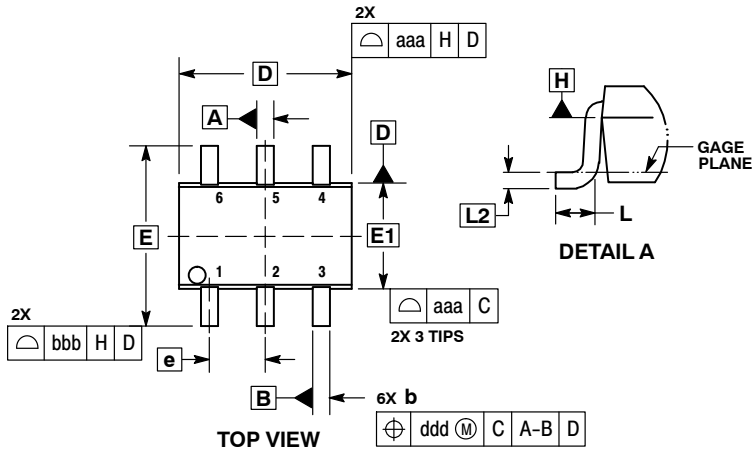
Device	Package	Shipping†
NTJS3157NT1G	SC-88 (Pb-Free)	3000 / Tape & Reel
NTJS3157NT2G	SC-88 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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PACKAGE DIMENSIONS

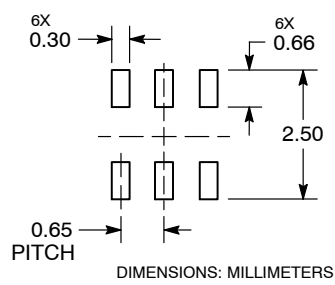
SC-88/SC70-6/SOT-363
CASE 419B-02
ISSUE Y



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.20 PER END.
 4. DIMENSIONS D AND E1 AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY AND DATUM H.
 5. DATUMS A AND B ARE DETERMINED AT DATUM H.
 6. DIMENSIONS b AND c APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN 0.08 AND 0.15 FROM THE TIP.
 7. DIMENSION b DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 TOTAL IN EXCESS OF DIMENSION b AT MAXIMUM MATERIAL CONDITION. THE DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OF THE FOOT.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	---	---	1.10	---	---	0.043
A1	0.00	---	0.10	0.000	---	0.004
A2	0.70	0.90	1.00	0.027	0.035	0.039
b	0.15	0.20	0.25	0.006	0.008	0.010
C	0.08	0.15	0.22	0.003	0.006	0.009
D	1.80	2.00	2.20	0.070	0.078	0.086
E	2.00	2.10	2.20	0.078	0.082	0.086
E1	1.15	1.25	1.35	0.045	0.049	0.053
e	0.65 BSC			0.026 BSC		
L	0.26	0.36	0.46	0.010	0.014	0.018
L2	0.15 BSC			0.006 BSC		
aaa	0.15			0.006		
bbb	0.30			0.012		
ccc	0.10			0.004		
ddd	0.10			0.004		

RECOMMENDED SOLDERING FOOTPRINT*



- STYLE 28:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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